NSN 5962-01-033-0745

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View Online at https://aerobasegroup.com/nsn/5962-01-033-0745						
Body Length:						
0.896 inches						
Body Width:						
Between 0.220 inches and 0.310 inches						
Body Height:						
Between 0.140 inches and 0.185 inches						
Maximum Power Dissipation Rating:						
625.0 milliwatts						
Operating Tempurature Range:						
-55.0/+125.0 degrees celsius						
Storage Tempurature Range:						
-65.0/+150.0 degrees celsius						
End Application:						
Bldg block 57 fscm 30003						
Features Provided:						
Hermetically sealed and monolithic and positive outputs and w/enable and programmable and programmed and bipolar and w/buffered						
output and w/decoded output and expandable and high speed and wire-or outputs						
Inclosure Material:						
Ceramic and glass						
Inclosure Configuration:						
Dual-in-line Dual-in-line						
Output Logic Form:						
Transistor-transistor logic						
Input Circuit Pattern:						
6 input						
Case Outline Source And Designator:						
D-2 mil-m-38510						
Terminal Surface Treatment:						
Solder						
Voltage Rating And Type Per Characteristic:						
-1.5 volts power source and 5.5 volts power source						
Time Rating Per Chacteristic:						
50.00 nanoseconds propagation delay time, low to high level output						
Memory Device Type:						
Rom						
Memory Capacity:						
Unknown						
Test Data Document:						
06424-10842 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.						

excludes any specification, standard or other document that may be referenced in a basic governing drawing)

16 printed circuit

Terminal Type And Quantity:

Shelf Life:

N/a

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In	18	<i>(</i>)+	МЛО	201	ure:

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Demilitarization:

Yes - demil/mli

Fiig:

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